Joseph Salfi

List of Publications by Year
in descending order

32 papers	809 citations	471061 17 h-index	525886 27 g-index
32 all docs	32 docs citations	32 times ranked	1025 citing authors

#	Article	IF	Citations
1	Shallow dopant pairs in silicon: An atomistic full configuration interaction study. Physical Review B, 2022, 105, .	1.1	4
2	Engineering long spin coherence times of spinâ€"orbit qubits in silicon. Nature Materials, 2021, 20, 38-42.	13.3	40
3	Roadmap on quantum nanotechnologies. Nanotechnology, 2021, 32, 162003.	1.3	45
4	Optimal operation points for ultrafast, highly coherent Ge hole spin-orbit qubits. Npj Quantum Information, 2021, 7, .	2.8	45
5	Novel characterization of dopant-based qubits. MRS Bulletin, 2021, 46, 616-622.	1.7	4
6	Certification of spin-based quantum simulators. Physical Review A, 2020, 101, .	1.0	0
7	Scanned Single-Electron Probe inside a Silicon Electronic Device. ACS Nano, 2020, 14, 9449-9455.	7.3	6
8	Hole spin echo envelope modulations. Physical Review B, 2019, 100, .	1.1	6
9	Two-electron states of a group-V donor in silicon from atomistic full configuration interactions. Physical Review B, 2018, 97, .	1.1	18
10	Readout and control of the spin-orbit states of two coupled acceptor atoms in a silicon transistor. Science Advances, 2018, 4, eaat9199.	4.7	26
11	Entanglement control and magic angles for acceptor qubits in Si. Applied Physics Letters, 2018, 113, .	1.5	11
12	Towards visualisation of central-cell-effects in scanning tunnelling microscope images of subsurface dopant qubits in silicon. Nanoscale, 2017, 9, 17013-17019.	2.8	5
13	Quantum simulation of the Hubbard model with dopant atoms in silicon. Nature Communications, 2016, 7, 11342.	5.8	81
14	Quantum computing with acceptor spins in silicon. Nanotechnology, 2016, 27, 244001.	1.3	31
15	A single-atom spin-orbit qubit in Si (Conference Presentation). , 2016, , .		0
16	Charge-Insensitive Single-Atom Spin-Orbit Qubit in Silicon. Physical Review Letters, 2016, 116, 246801.	2.9	44
17	Spatial metrology of dopants in silicon with exact lattice site precision. Nature Nanotechnology, 2016, 11, 763-768.	15.6	45
18	Spatially resolved resonant tunneling on single atoms in silicon. Journal of Physics Condensed Matter, 2015, 27, 154203.	0.7	20

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19	Donor hyperfine Stark shift and the role of central-cell corrections in tight-binding theory. Journal of Physics Condensed Matter, 2015, 27, 154207.	0.7	16
20	Spatially resolving valley quantum interference of a donor in silicon. Nature Materials, 2014, 13, 605-610.	13.3	90
21	Probing the Spin States of a Single Acceptor Atom. Nano Letters, 2014, 14, 1492-1496.	4.5	36
22	Probing a single acceptor in a silicon nanotransistor. , 2014, , .		0
23	Probing the Gateâ^'Voltage-Dependent Surface Potential of Individual InAs Nanowires Using Random Telegraph Signals. ACS Nano, 2011, 5, 2191-2199.	7.3	20
24	Electrical characteristics and photocurrent spectral response of Si nanowires p-i-n junctions. Optics Express, 2011, 19, 5464.	1.7	4
25	Transport and strain relaxation in wurtzite InAsâ€"GaAs core-shell heterowires. Applied Physics Letters, 2011, 98, .	1.5	57
26	Direct observation of single-charge-detection capability of nanowire field-effect transistors. Nature Nanotechnology, 2010, 5, 737-741.	15.6	49
27	Room temperature single nanowire ZnTe photoconductors grown by metal-organic chemical vapor deposition. Applied Physics Letters, 2010, 97, 063510.	1.5	29
28	(Invited) Optical Response of II-VI ZnSe Nanowires. ECS Transactions, 2010, 28, 193-202.	0.3	2
29	Electrical characteristics and photocurrent spectral response of Si nanowires p-i-n junctions. , 2010, , .		0
30	Carrier transport in molecular beam epitaxially grown GaAs/InAs core-shell nanowires. , 2010, , .		2
31	Transport and optical response of single nanowires. Journal of Materials Science: Materials in Electronics, 2009, 20, 480-486.	1.1	3
32	Electrical properties of Ohmic contacts to ZnSe nanowires and their application to nanowire-based photodetection. Applied Physics Letters, 2006, 89, 261112.	1.5	70